

Amendments to the Claims:

Claim 1 has been amended herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

1. (Currently Amended) A ~~process~~ method for making a transistor comprising:
providing a substrate;
forming a dielectric layer on a portion of the substrate;
forming a gate structure on the dielectric layer having a transition ~~gate-oxide~~ layer formed on the dielectric layer and a metal silicide layer formed on the transition ~~gate-oxide~~ layer, the gate structure having a first sidewall and a second sidewall, the first sidewall and the second sidewall defining therebetween within the substrate a first contact region, a channel region and a second contact region; and
forming first, second, and third subregions within the second contact region, each subregion having a dopant concentration that differs from that of the other two subregions, forming of the first, second, and third subregions comprising:
depositing a conformal layer of dielectric material having a first thickness over the substrate;
anisotropically etching the conformal layer of dielectric material, forming a layer of dielectric material on the first sidewall and the second sidewall;
subjecting the layer of dielectric material on the first sidewall and the second sidewall to an annealing/oxidation process;
forming a single layer sidewall spacer having a second thickness greater than the first thickness of the dielectric material overlying the first sidewall and the second sidewall;
introducing a first dopant into the substrate to form the first subregion;
forming another single layer sidewall spacer overlying the single layer sidewall spacer, the another single layer sidewall spacer having a third thickness intermediate the

first thickness of the dielectric layer and the second thickness of the single layer sidewall spacer;

introducing a second dopant into the substrate to form the second subregion;
substantially removing the another single layer sidewall spacer; and
introducing a third dopant into the substrate to form the third subregion.

2. (Previously Presented) The method of claim 1, wherein the single layer sidewall spacer comprises a layer having a thickness in the range of between about 50 and 150 Angstroms.

3. (Previously Presented) The method of claim 1, wherein the another single layer sidewall spacer comprises a layer of material having a thickness in the range of about 2 to 20 times a thickness of the single layer sidewall spacer.

4. (Previously Presented) The method of claim 1, wherein the another single layer sidewall spacer comprises a layer of material having a thickness of about 550 Angstroms.

5. (Previously Presented) The method of claim 1, wherein the another single layer sidewall spacer comprises a material of one of silicon nitride and silicon dioxide.